DESCRIPTION

~~SOLAR CELL AND SOLAR CELL MANUFACTURING METHOD~~

TECHNICAL FIELD

[0001]

The present invention relates to a solar cell and a method for manufacturing a solar cell.

BACKGROUND ART

[0002]

Solar cells using silicon substrates doped with boron (B) have a problem of lowering the conversion efficiency due to photo-irradiation. On the other hand, it has been known that solar cells using silicon substrates doped with gallium (Ga) do not occur photo-degradation (e.g., see Patent Document 1).

[0003]

On the other hand, as a surface passivation method of a silicon substrate, silicon thermal oxide films have long been known to possess excellent properties.

CITATION LIST

PATENT LITERATURE

[0004]

Patent Document 1: Japanese Patent No. 3679366

SUMMARY OF INVENTION

PROBLEM TO BE SOLVED BY THE INVENTION

[0005]

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